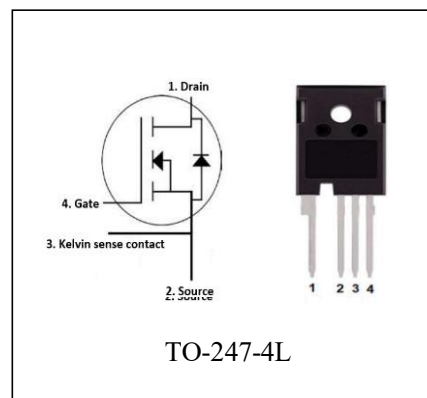


1. Description

SS13C120W4P is an N-channel enhancement type planar MOSFET, with the revolutionary semiconductor material - silicon carbide, which has the advantages of low on-resistance, low capacitance and gate charge, and superior switching performance. The device can provide higher efficiency, faster operation frequency and compact system size for power-electronic system application compared to Silicon.

KEY CHARACTERISTICS

Parameter	Value	Unit
V_{DS}	1200	V
I_D	152	A
$R_{DS(ON).Typ}$	13	mΩ



FEATURES

- Revolutionary semiconductor material - Silicon Carbide
- High blocking voltage with low on-resistance
- Fast intrinsic diode with low reverse recovery
- Low switching losses
- 100% Avalanche Tested
- RoHS product

APPLICATIONS

- Motor Control
- EV Battery Chargers
- High Voltage DC-DC Converter

ORDERING INFORMATION

Ordering Codes	Package	Product Code	Packing
SS13C120WP4	TO-247-4L	SS13C120WP4	Tube